

## IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the above-referenced application.

1. (Original) A structure comprising:  
a semiconductor light emitting device comprising a light emitting layer disposed between an n-type region and a p-type region, the light emitting layer configured to emit light of a first wavelength; and  
a cerium-doped garnet phosphor having a cerium concentration between about 4 mol% and about 8 mol%.
2. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor has a cerium concentration of about 6 mol%.
3. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is  $(\text{Lu}_{1-x-y-a-b}\text{Y}_x\text{Gd}_y)_3(\text{Al}_{1-z}\text{Ga}_z)_5\text{O}_{12}:\text{Ce}_a\text{Pr}_b$  wherein  $0 < x < 1$ ,  $0 < y < 1$ ,  $0 < z \leq 0.1$ ,  $0 < a \leq 0.2$  and  $0 < b \leq 0.1$ .
4. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is  $\text{Y}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$ .
5. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is disposed to absorb light of the first wavelength and capable of absorbing light of the first wavelength and emitting light of a second wavelength.
6. (Original) The structure of claim 5 wherein the first wavelength is blue and the second wavelength ranges from green to yellow.
7. (Original) The structure of claim 5 wherein the cerium-doped garnet phosphor is a first wavelength converting material, the structure further comprising a second wavelength-converting material, wherein the second wavelength-converting material is capable of absorbing light of one of the first wavelength and the second wavelength and emitting light of a third wavelength longer than the second wavelength.
8. (Original) The structure of claim 7 wherein the third wavelength is red.
9. (Original) The structure of claim 7 wherein the second wavelength converting material is one of  $(\text{Ca}_{1-x}\text{Sr}_x)\text{S}:\text{Eu}^{2+}$  wherein  $0 < x \leq 1$ ;  $\text{CaS}:\text{Eu}^{2+}$ ;  $\text{SrS}:\text{Eu}^{2+}$ ;  $(\text{Sr}_{1-x-y}\text{Ba}_x\text{Ca}_y)_2\text{-zSi}_{5-a}\text{Al}_a\text{N}_{8-a}\text{O}_a:\text{Eu}_z^{2+}$  wherein  $0 \leq a < 5$ ,  $0 < x \leq 1$ ,  $0 \leq y \leq 1$ , and  $0 < z \leq 1$ ; and  $\text{Sr}_2\text{Si}_5\text{N}_8:\text{Eu}^{2+}$ .
10. (Original) The structure of claim 1 wherein the semiconductor light emitting device is a III-nitride light emitting diode.

11. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is coated on a top surface and a side surface of the light emitting device.

12. (Original) The structure of claim 1 further comprising:  
a pair of leads electrically connected to the light emitting device; and  
a lens disposed over the light emitting device.

13. (Original) The structure of claim 12 wherein the cerium-doped garnet phosphor is dispersed in an encapsulant disposed between the light emitting device and the lens.

14. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is spaced apart from the light emitting device.